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Details

Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	48MHz
Connectivity	I²C, SCI, SPI, USB
Peripherals	LVD, POR, PWM, WDT
Number of I/O	46
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 8x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08mm128clk

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Related Documentation

Find the most current versions of all documents at: http://www.freescale.com.

Reference Manual —MC9S08MM128RM

Contains extensive product information including modes of operation, memory, resets and interrupts, register definition, port pins, CPU, and all module information.

Devices in the MC9S08MM128 series

A complete description of the modules included on each device is provided in the following table.

Module	Version
Analog-to-Digital Converter (ADC16)	1
General Purpose Operational Amplifier (OPAMP)	1
Trans-Impedance Operational Amplifier (TRIAMP)	1
Digital to Analog Converter (DAC)	1
Programmable Delay Block	1
Inter-Integrated Circuit (IIC)	3
Central Processing Unit (CPU)	5
On-Chip In-Circuit Debug/Emulator (DBG)	3
Multi-Purpose Clock Generator (MCG)	3
Low Power Oscillator (XOSCVLP)	1
Carrier Modulator Timer (CMT)	1
Programable Analog Comparator (PRACMP)	1
Serial Communications Interface (SCI)	4
Serial Peripheral Interface (SPI)	5
Time of Day (TOD)	1
Universal Serial Bus (USB) ¹	1
Timer Pulse-Width Modulator (TPM)	3
System Integration Module (SIM)	1
Cyclic Redundancy Check (CRC)	3
Keyboard Interrupt (KBI)	2
Voltage Reference (VREF)	1
Voltage Regulator (VREG)	1
Interrupt Request (IRQ)	3
Flash Wrapper	1
GPIO	2
Port Control	1

Table 2. Versions of On-Chip Module

¹ USB Module not available on MC9S08MM32A devices.

The block diagram in Figure 1 shows the structure of the MC9S08MM128 series MCU.

Devices in the MC9S08MM128 series

1.1 Pin Assignments

This section shows the pin assignments for the MC9S08MM128 series devices.

1.1.1 64-Pin LQFP

The following two figures show the 64-pin LQFP pinout configuration. The first illustrates the pinout configuration for MC9S08MM128, MC9S08MM64, and MC9S08MM32 devices.

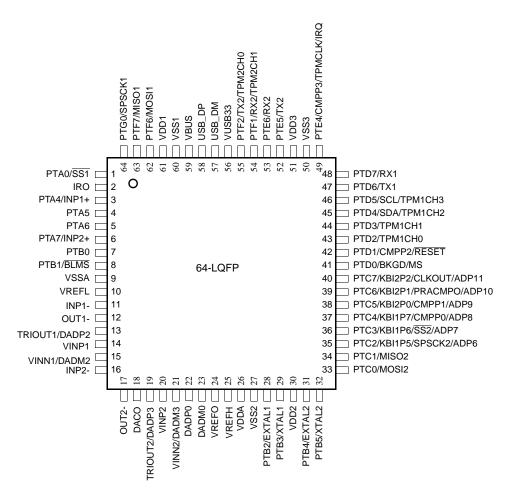


Figure 2. 64-Pin LQFP for MC9S08MM128, MC9S08MM64, and MC9S08MM32 devices

For MC9S08MM32A devices, pins 56, 57, 58, and 59 are no connects (NC) as illustrated in the following figure.

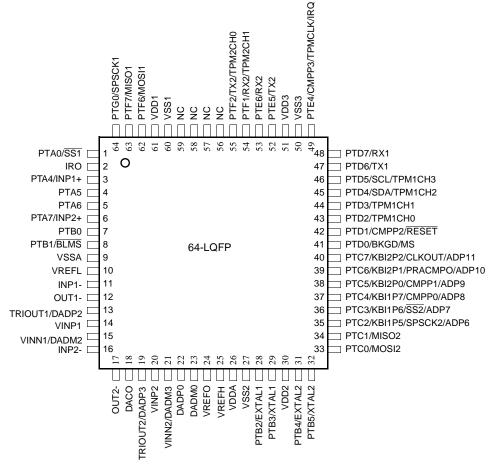


Figure 3. 64-Pin LQFP for MC9S08MM32A devices

Freescale Semiconductor

1.1.3 81-Pin MAPBGA

The following figure shows the 81-pin MAPBGA pinout configuration.

	1	2	3	4	5	6	7	8	9
A	IRO	PTG0	PTF6	USB_DP	VBUS	VUSB33	PTF4	PTF3	PTE4
в	PTF7	PTA0	PTG1	USB_DM	PTF5	PTE7	PTF1	PTF0	PTE3
с	PTA4	PTA5	PTA6	PTA1	PTF2	PTE6	PTE5	PTE2	PTE1
D	INP1-	PTA7	PTB0	PTB1	PTA2	PTA3	PTD5	PTD7	PTE0
Е	OUT1	VINN1	OUT2	VDD2	VDD3	VDD1	PTD2	PTD3	PTD6
F	VINP1	TRIOUT1	INP2-	VSS2	VSS3	VSS1	PTB7	PTC7	PTD4
G	DADP0	DACO	TRIOUT2	VINN2	VREFO	PTB6	PTC0	PTC1	PTC2
н	DADMO	DADM1	DADP1	VINP2	PTC3	PTC4	PTD0	PTC5	PTC6
J	VSSA	VREFL	VREFH	VDDA	PTB2	PTB3	PTD1	PTB4	PTB5

Figure 5. 81-Pin MAPBGA

This section contains electrical specification tables and reference timing diagrams for the MC9S08MM128/64/32/32A microcontroller, including detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications.

The electrical specifications are preliminary and are from previous designs or design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. These specifications will, however, be met for production silicon. Finalized specifications will be published after complete characterization and device qualifications have been completed.

NOTE

The parameters specified in this data sheet supersede any values found in the module specifications.

2.1 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 4. Parameter Classifications

Р	Those parameters are guaranteed during production testing on each individual device.
с	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

2.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in the following table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

#	Rating	Symbol	Value	Unit
1	Supply voltage	V _{DD}	-0.3 to +3.8	V
2	Maximum current into V _{DD}	I _{DD}	120	mA
3	Digital input voltage	V _{In}	-0.3 to V _{DD} + 0.3	V
4	Instantaneous maximum current Single pin limit (applies to all port pins) ^{1, 2, 3}	Ι _D	± 25	mA
5	Storage temperature range	T _{stg}	-55 to 150	°C

Table 5.	Absolute	Maximum	Ratings
----------	----------	---------	---------

¹ Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

 $^2\,$ All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

³ Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}).

Num	Symbol	Charac	teristic	Condition	Min	Typ ¹	Max	Unit	С
7	VIL	Input low voltage	all digital inputs						<u> </u>
				all digital inputs, $V_{DD} > 2.7 \ V$		—	0.35 x V _{DD}	V	Р
				all digital inputs, $\begin{array}{l} 2.7 > V_{DD} \geq 1.8 \\ V \end{array}$	_	_	0.30 x V _{DD}	V	Р
8	V _{hys}	Input hysteresis	all digital inputs	—	0.06 x V _{DD}	—	—	mV	С
9	I _{In}	Input leakage current	all input only pins (Per pin)	$V_{In} = V_{DD} \text{ or } V_{SS}$	_	_	0.5	μΑ	Ρ
10	I _{OZ}	Hi-Z (off-state) leakage current ³	all digital input/output (per pin)	$V_{In} = V_{DD} \text{ or } V_{SS}$	_	0.003	0.5	μΑ	Ρ
11	R _{PU}	Pull-up resistors	-	—	17.5	—	52.5	kΩ	Р
12	R _{PD}	Internal pull-down resistors ⁴		_	17.5	_	52.5	kΩ	Р
13	I _{IC}	DC injection current ^{5, 6, 7}	Single pin limit			1			
				$V_{SS} > V_{IN} > V_{DD}$	-0.2	—	0.2	mA	D
			Total MCU limit,	includes sum of a	Il stressed pins	S			
				$V_{SS} > V_{IN} > V_{DD}$	-5	_	5	mA	D
14	C _{In}	Input Capacitance	e, all pins	—	_	—	8	pF	С
15	V _{RAM}	RAM retention vo	tage	—	_	0.6	1.0	V	С
16	V _{POR}	POR re-arm volta	ge ⁸	—	0.9	1.4	1.79	V	С
17	t _{POR}	POR re-arm time		—	10	—	—	μS	D
18	V _{LVDH} 9	Low-voltage V _{DD} falling detection threshold — high range							
				—	2.11	2.16	2.22	V	Р
			V_{DD} rising						
				_	2.16	2.23	2.27	V	Р
19	V _{LVDL}	Low-voltage V _{DD} falling detection threshold — low range ⁹							
				_	1.80	1.84	1.88	V	Р
			V _{DD} rising						
				—	1.88	1.93	1.96	V	Р

Table 9. DC Characteristics (Continued)

#	Symb	Characteristic	Conditions	Min	Typ ¹	Max	Unit	С	Comment
10	f _{ADCK}	ADC Conversion (Frequency	Clock		1	L			
		ADLPC=0, ADHS	1.0	_	8.0	MHz	D		
		ADLPC=0, ADHSC=0		1.0	_	5.0	MHz	D	
		ADLPC=1, ADHSC=0		1.0	_	2.5	MHz	D	

¹ Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

² DC potential difference.

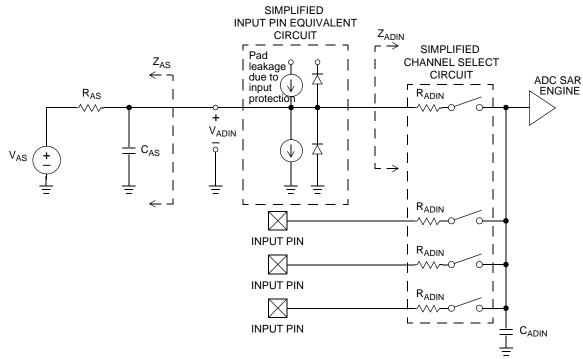


Figure 7. ADC Input Impedance Equivalency Diagram

Table 16. 16-Bit SAR ADC Characteristics full operating range
(V _{REFH} = V _{DDA} , > 1.8, V _{REFL} = V _{SSA} \leq 8 MHz, –40 to 85 °C)

#	Characteristic	Conditions ¹	Symb	Min	Typ ²	Max	Unit	с	Comment
	Supply Current	ADLPC=1, ADHSC=0		_	215	_			
1		ADLPC=0, ADHSC=0	I _{DDAD}		470	—	μA	т	ADLSMP =0
		ADLPC=0, ADHSC=1		_	610	—			ADCO=1
2	Supply Current	Stop, Reset, Module Off	I _{DDAD}	—	0.01	—	μΑ	Т	
	ADC	ADLPC=1, ADHSC=0		_	2.4	—			
3	Asynchronous Clock Source	ADLPC=0, ADHSC=0	f _{ADACK}		5.2	—	MHz	С	t _{ADACK} =
		ADLPC=0, ADHSC=1		_	6.2	—			1/f _{ADACK}
4	Sample Time	See Reference Manual for	sample tim	nes					
5	Conversion Time	See Reference Manual for	conversion	i times					
6	Total Unadjusted Error	16-bit differential mode 16-bit single-ended mode	TUE		±16 ±20	+48/ -40 +56/ -28	LSB ³	Т	32x Hardware Averaging (AVGE = %1 AVGS = %11)
		13-bit differential mode 12-bit single-ended mode		_	±1.5 ±1.75	±3.0 ±3.5		Т	
		11-bit differential mode 10-bit single-ended mode		_	±0.7 ±0.8	±1.5 ±1.5		Т	
		9-bit differential mode 8-bit single-ended mode		_	±0.5 ±0.5	±1.0 ±1.0		Т	
7	Differential Non-Linearity	16-bit differential mode 16-bit single-ended mode	DNL	_	±2.5 ±2.5	+5/-3 +5/-3	LSB ²	Т	
		13-bit differential mode 12-bit single-ended mode		_	±0.7 ±0.7	±1 ±1		Т	
		11-bit differential mode 10-bit single-ended mode		_	±0.5 ±0.5	±0.75 ±0.75		Т	
		9-bit differential mode 8-bit single-ended mode			±0.2 ±0.2	±0.5 ±0.5		Т	

2.10 MCG and External Oscillator (XOSC) Characteristics

#	Rating		Symbol	Min	Typical	Мах	Unit	С
1	Internal reference startup time		t _{irefst}		55	100	μS	D
2	Average internal reference frequency	factory trimmed at VDD=3.0 V and temp=25°C	f _{int_ft}	_	31.25	_	kHz	С
		user trimmed		31.25	—	39.0625		С
3	DCO output frequency range —	Low range (DRS=00)	filment	16		20	μs kHz MHz %f _{dco} %f _{dco} ms %f _{dco} MHz MHz %f _{pll}	С
U	trimmed	Mid range (DRS=01)	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	101112	С			
		High range ¹ (DRS=10)		40	—	60	μs kHz MHz %f _{dco} %f _{dco} ms %f _{dco} MHz MHz %f _{pll} %	С
4	Resolution of trimmed DCO output fre-	with FTRIM	Af .	_	± 0.1	± 0.2	%f.	С
4	quency at fixed voltage and tempera- ture	without FTRIM	[∆] 'dco_res_t	_	± 0.2	± 0.4	⁷⁰¹ dco	С
	Total deviation of trimmed DCO output	over voltage and temperature		_	±1.0	±2		Ρ
5	frequency over voltage and tempera- ture	over fixed voltage and temp range of 0 – 70 °C	Δf_{dco_t}	_	± 0.5	± 1	μs kHz MHz %f _{dco} %f _{dco} MHz MHz %f _{pll} % % kHz	С
~	Acquisition time	FLL ²	t _{fll_acquire}		—	1		С
6		PLL ³		_		1	ms	D
7	Long term Jitter of DCO output clock (a interval) 4	averaged over 2mS	C _{Jitter}	_	0.02	0.2	%f _{dco}	С
8	VCO operating frequency		f _{vco}	7.0	—	55.0	MHz	D
9	PLL reference frequency range		f _{pll_ref}	1.0	—	2.0	MHz	D
10	Jitter of PLL output clock measured over 625ns 5	Long term		_	0.566 ⁴	_	%f _{pll}	D
4.4		Entry ⁶	D _{lock}	± 1.49	—	± 2.98	0/	D
11	Lock frequency tolerance	Exit ⁷	D _{unl}	± 4.47	—	± 5.97	70	D
		FLL	t _{fll_lock}	_	_	t _{fll_acquire+} 1075(1/ ^f int_t)	 %f_{dco} %f_{dco} ms %f_{dco} MHz %f_{pil} %f_{pil} %s kHz 	D
12	Lock time	PLL	t _{pll_lock}	_	_	t _{pll_acquire+} 1075(1/ ^f pll_re f)	S	D
13	Loss of external clock minimum freque	ncy - RANGE = 0	f _{loc_low}	(3/5) x f _{int_t}	_	_	kHz	D
14	Loss of external clock minimum freque	ncy - RANGE = 1	f _{loc_high}	(16/5) x f _{int_t}	_	_	kHz	D

Table 18. MCG (Temperature Range = -40 to 105°C Ambient)

¹ This should not exceed the maximum CPU frequency for this device which is 48 MHz.

² This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bit is changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

- ³ This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- ⁴ Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{BUS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.
- ⁵ 625 ns represents 5 time quanta for CAN applications, under worst-case conditions of 8 MHz CAN bus clock, 1 Mbps CAN Bus speed, and 8 time quanta per bit for bit time settings. 5 time quanta is the minimum time between a synchronization edge and the sample point of a bit using 8 time quanta per bit.
- ⁶ Below D_{lock} minimum, the MCG is guaranteed to enter lock. Above D_{lock} maximum, the MCG will not enter lock. But if the MCG is already in lock, then the MCG may stay in lock.
- ⁷ Below D_{unl} minimum, the MCG will not exit lock if already in lock. Above D_{unl} maximum, the MCG is guaranteed to exit lock.

#	Chara	acteristic	Symbol	Min	Typ ¹	Max	Unit	С
	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1)	• Low range (RANGE = 0)	f _{lo}	32	_	38.4	kHz	D
		 High range (RANGE = 1), FEE or FBE mode ² 	f _{hi-fll}	1	_	5	MHz	D
1		 High range (RANGE = 1), PEE or PBE mode ³ 	f _{hi-pll}	1	—	16	MHz	D
		 High range (RANGE = 1), High gain (HGO = 1), BLPE mode 	f _{hi-hgo}	1	_	16	MHz	D
		 High range (RANGE = 1), Low power (HGO = 0), BLPE mode 	f _{hi-lp}	1	_	8	MHz	D
2	Load capacitors		C ₁ C ₂	See crys	stal or resona recommer		cturer's	D
3	Feedback resistor	 Low range (32 kHz to 38.4 kHz) 	R _F	_	10	—	MΩ	D
3		High range (1 MHz to 16 MHz)	-		1	—	1015.2	D
4	Series resistor — Low range	• Low Gain (HGO = 0)	R _S		0		kΩ	D
4		• High Gain (HGO = 1)			100			D
	Series resistor — High range	• Low Gain (HGO = 0)	R _S	_	0			D
		• High Gain (HGO = 1)					1	D
5		≥ 8 MHz		—	0	0	kΩ	D
		4 MHz			0	10		D
		1 MHz		—	0	20		D

Table 19. XOSC (Temperature Range = -40 to 105°C Ambient)

#	Charae	cteristic	Symbol	Min	Typ ¹	Max	Unit	С
	Crystal start-up time ⁴	• Low range, low gain (RANGE = 0, HGO = 0)	t CSTL-LP	_	200	_		D
		 Low range, high gain (RANGE = 0, HGO = 1) 	t CSTL-HG O	_	400	_		D
6		 High range, low gain (RANGE = 1, HGO = 0)⁵ 	t _{CSTH-LP}	_	5	_	ms	D
		 High range, high gain (RANGE = 1, HGO = 1)⁵ 	^t CSTH-HG О	_	15	_	ms	D

Table 19. XOSC (Temperature Range = -40 to 105°C Ambient)

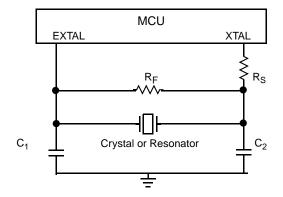
¹ Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

² When MCG is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

³ When MCG is configured for PEE or PBE mode, input clock source must be divisible using RDIV to within the range of 1 MHz to 2 MHz.

⁴ This parameter is characterized and not tested on each device. Proper PC board layout porcedures must be followed to achieve specifications.

⁵ 4 MHz crystal.



2.11.2 TPM Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 21. TPM Input Timing

#	С	Function	Symbol	Min	Мах	Unit
1	—	External clock frequency	f _{TPMext}	dc	f _{Bus} /4	MHz
2	—	External clock period	t _{TPMext}	4	—	t _{cyc}
3	D	External clock high time	t _{clkh}	1.5	_	t _{cyc}
4	D	External clock low time	t _{clkl}	1.5	—	t _{cyc}
5	D	Input capture pulse width	t _{ICPW}	1.5	—	t _{cyc}

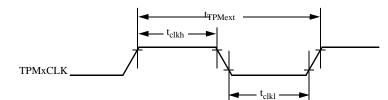


Figure 10. Timer External Clock

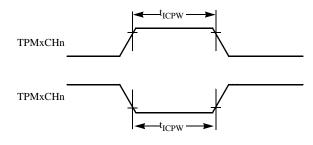
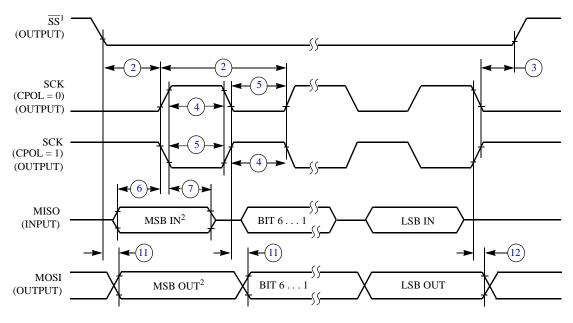


Figure 11. Timer Input Capture Pulse

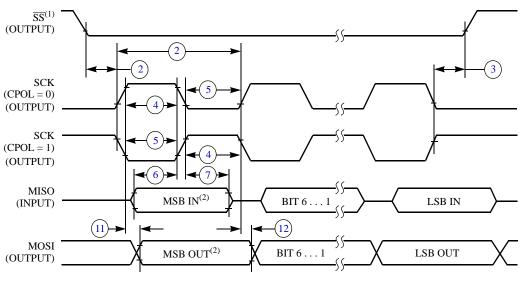


NOTES:

1. \overline{SS} output mode (MODFEN = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.



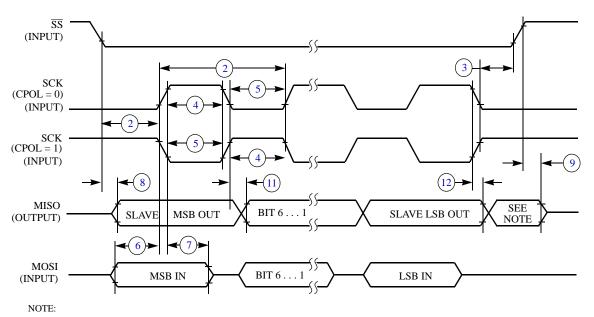


NOTES:

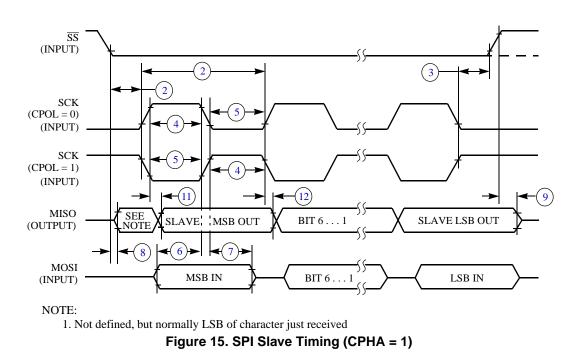
1. \overline{SS} output mode (MODFEN = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 13. SPI Master Timing (CPHA = 1)



1. Not defined, but normally MSB of character just received **Figure 14. SPI Slave Timing (CPHA = 0)**



2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory chapter in the Reference Manual for this device (MC9S08MM128RM).

#	Characteristic	Symbol	Min	Typical	Мах	Unit	С
1	Supply voltage for program/erase –40°C to 105°C	V _{prog/erase}	1.8	_	3.6	V	D
2	Supply voltage for read operation	V _{Read}	1.8	—	3.6	V	D
3	Internal FCLK frequency ¹	f _{FCLK}	150	_	200	kHz	D
4	Internal FCLK period (1/FCLK)	t _{Fcyc}	5		6.67	μS	D
5	Byte program time (random location) ²	t _{prog}		9		t _{Fcyc}	Р
6	Byte program time (burst mode) ²	t _{Burst}		4		t _{Fcyc}	Р
7	Page erase time ²	t _{Page}		4000		t _{Fcyc}	Р
8	Mass erase time ²	t _{Mass}		20,000		t _{Fcyc}	Р
9	Program/erase endurance ³ T _L to T _H = -40° C to + 105° C T = 25° C		10,000	 100,000	_	cycles	С
10	Data retention ⁴	t _{D_ret}	15	100		years	С

Table 23. Flash Characteristics

¹ The frequency of this clock is controlled by a software setting.

² These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

³ **Typical endurance for flash** was evaluated for this product family on the HC9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory*.

⁴ Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618, *Typical Data Retention for Nonvolatile Memory.*

2.14 USB Electricals

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit http://www.usb.org.

If the Freescale USB On-the-Go implementation has electrical characteristics that deviate from the standard or require additional information, this space would be used to communicate that information.

#	Characteristic	Symbol	Min	Тур	Мах	Unit	С
1	Regulator operating voltage	V _{regin}	3.9	_	5.5	V	С
2	VREG output	V _{regout}	3	3.3	3.75	V	Р
3	V _{USB33} input with internal VREG disabled	V _{usb33in}	3	3.3	3.6	V	С
4	VREG Quiescent Current	I _{VRQ}	_	0.5	_	mA	С

Table 24. Internal USB 3.3 V Voltage Regulator Characteristics

2.16 TRIAMP Electrical Parameters

Table 27. TRIAMP Characteristics 1.8–3.6 V, –40°C~105°C

#	Characteristic ¹	Symbol	Min	Typ ²	Max	Unit	С
1	Operating Voltage	V _{DD}	1.8	—	3.6	V	С
2	Supply Current (I _{OUT} =0mA, CL=0) Low-power mode	I _{SUPPLY}		52	60	μA	Т
3	Supply Current (I _{OUT} =0mA, CL=0) High-speed mode	I _{SUPPLY}	_	432	480	μΑ	Т
4	Input Offset Voltage	V _{OS}		± 1	± 5	mV	Т
5	Input Offset Voltage Temperature Drift	α _{VOS}		600	—	μV	Т
6	Input Offset Current	I _{OS}		±120	500	pА	Т
7	Input Bias Current (0 ~ 50°C)	I _{BIAS}	_	< 350	< ±500	pА	Т
8	Input Bias Current (–40 ~ 105°C)	I _{BIAS}		3	6.55	nA	Т
9	Input Common Mode Voltage Low	V _{CML}	0	—	—	V	Т
10	Input Common Mode Voltage High	V _{CMH}		—	V _{DD} -1.4	V	Т
11	Input Resistance	R _{IN}	500	—	—	MΩ	Т
12	Input Capacitances	C _{IN}		—	5	pF	D
13	AC Input Impedance (f _{IN} =100kHz)	X _{IN}	_	1	—	MΩ	D
14	Input Common Mode Rejection Ratio	CMRR	60	70	—	dB	Т
15	Power Supply Rejection Ration	PSRR	60	70	—	dB	Т
16	Slew Rate (ΔV_{IN} =100mV) Low-power mode	SR		0.1	—	V/µs	Т
17	Slew Rate (ΔV_{IN} =100mV) High-speed mode	SR	_	1	—	V/µs	Т
18	Unity Gain Bandwidth (Low-power mode) 50pF	GBW	0.15	0.25	—	MHz	Т
19	Unity Gain Bandwidth (High-speed mode) 50pF	GBW	_	1.6	—	MHz	Т
20	DC Open Loop Voltage Gain	A _V		80	—	dB	Т
21	Load Capacitance Driving Capability	CL(max)		—	100	pF	Т
22	Output Impedance AC Open Loop (@100 kHz Low-power mode)	R _{OUT}	_	1.4	—	kΩ	D
23	Output Impedance AC Open Loop (@100 kHz High-speed mode)	R _{OUT}	—	184	—	Ω	D
24	Output Voltage Range	triout	0.15	_	V _{DD} – 0.15	V	Т
25	Output Drive Capability	I _{OUT}	_	± 1.0	—	mA	Т
26	Gain Margin	GM	20		—	dB	D
27	Phase Margin	PM	45	55	_	deg	Т
28	Input Voltage Noise Density	f= 1 kHz	—	160	—	nV/√Hz	Т

¹ All parameters are measured at 3.0 V, CL= 47 pF across temperature -40 to + 105 °C unless specified.

 $^2\,$ Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

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